NPN Epitaxial Planar Silicon Transistor



30C01S

Low-Frequency General-Purpose Amplifier Applications

Applications

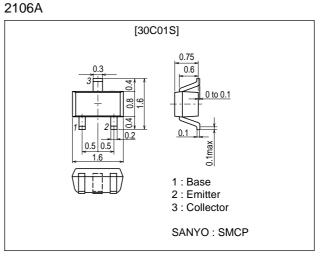
• Low-frequency Amplifier, muting circuit.

Features

- Large current capacitance.
- Low collector-to-emitter saturation voltage (resistance). $R_{CE}(sat)$ typ=0.70 Ω [IC=0.4A, IB=20mA].
- Ultrasmall package facilitates miniaturization in end products.
- Small ON-resistance (Ron).

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|--------|--|-------------|------|
| Collector-to-Base Voltage | VCBO | | 40 | V |
| Collector-to-Emitter Voltage | VCEO | | 30 | V |
| Emitter-to-Base Voltage | VEBO | | 5 | V |
| Collector Current | IC | | 400 | mA |
| Collector Current (Pulse) | ICP | | 800 | mA |
| Collector Dissipation | PC | Mounted on a glass epoxy board (20X30X1.6mm) | 200 | mW |
| Junction Temperature | Tj | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |

Electrical Characteristics at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit | |
|---|-----------------------|--|---------|-----|-----|------|--|
| | | | min | typ | max | Unit | |
| Collector Cutoff Current | ІСВО | V _{CB} =30V, I _E =0 | | | 0.1 | μΑ | |
| Emitter Cutoff Current | IEBO | VEB=4V, IC=0 | | | 0.1 | μA | |
| DC Current Gain | hFE | V _{CE} =2V, I _C =10mA | 300 | | 800 | | |
| Gain-Bandwidth Product | fT | V _{CE} =10V, I _C =50mA | | 380 | | MHz | |
| Output Capacitance | Cob | V _{CB} =10V, f=1MHz | | 2.4 | | pF | |
| Collector-to-Emitter Saturation Voltage | V _{CE} (sat) | IC=100mA, IB=5mA | | 100 | 200 | mV | |
| Base-to-Emitter Saturation Voltage | V _{BE} (sat) | IC=100mA, IB=5mA | | 0.9 | 1.2 | V | |
| Arking · YO | | | | | | | |

Marking : YQ

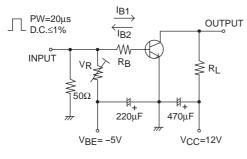
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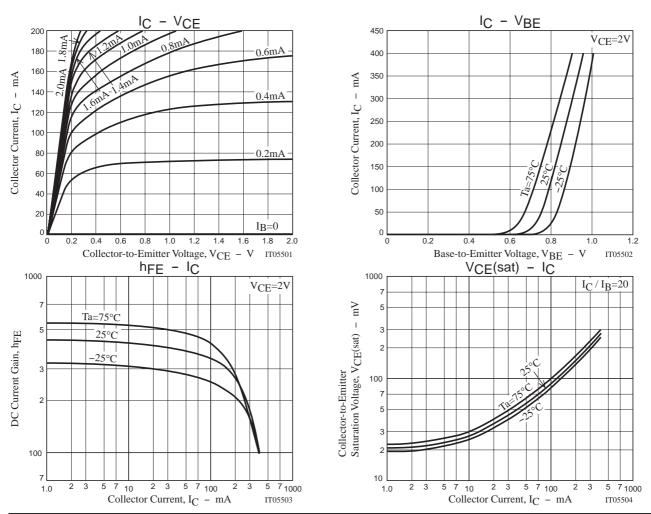
SANYO Electric Co., Ltd. Semiconductor Company TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN Continued from preceding page.

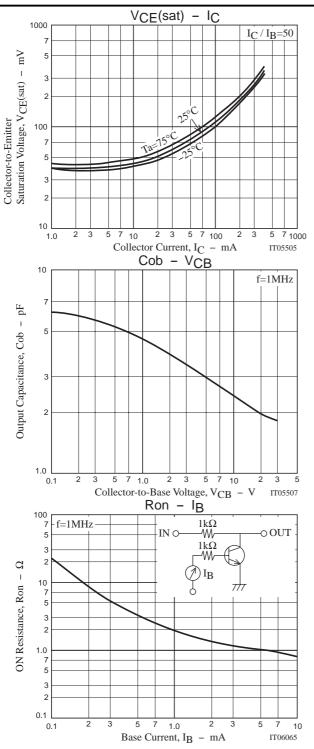
| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--|----------|-----------------------------|---------|-----|-----|------|
| | | | min | typ | max | Unit |
| Collector-to-Base Breakdown Voltage | V(BR)CBO | IC=10μA, IE=0 | 40 | | | V |
| Collector-to-Emitter Breakdown Voltage | V(BR)CEO | IC=1mA, R _{BE} =∞ | 30 | | | V |
| Emitter-to-Base Breakdown Voltage | V(BR)EBO | IE=10μA, IC=0 | 5 | | | V |
| Turn-ON Time | ton | See specified Test Circuit. | | 42 | | ns |
| Storage Time | tstg | See specified Test Circuit. | | 135 | | ns |
| Fall Time | tf | See specified Test Circuit. | | 90 | | ns |

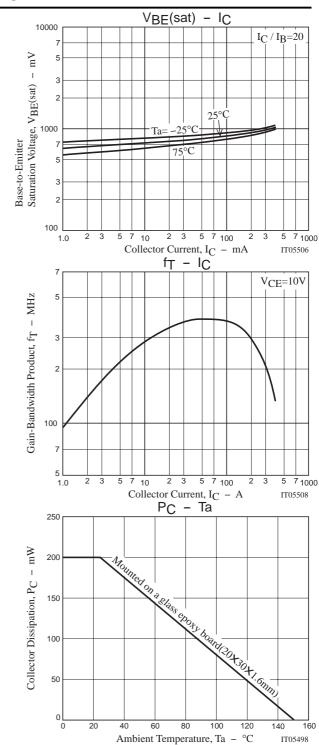
Switching Time Test Circuit



 $I_{C}=20I_{B1}=-20I_{B2}=300mA$







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